



SANYO Semiconductors

DATA SHEET

An ON Semiconductor Company

MCH6320 — P-Channel Silicon MOSFET — General-Purpose Switching Device Applications

Features

- Ultrahigh-speed switching
- 1.8V drive

Specifications

Absolute Maximum Ratings at Ta=25°C

Parameter	Symbol	Conditions	Ratings	Unit
Drain-to-Source Voltage	V _{DSS}		-12	V
Gate-to-Source Voltage	V _{GSS}		±10	V
Drain Current (DC)	I _D		-3.5	A
Drain Current (Pulse)	I _{DP}	PW≤10μs, duty cycle≤1%	-14	A
Allowable Power Dissipation	P _D	When mounted on ceramic substrate (1200mm ² ×0.8mm)	1.5	W
Channel Temperature	T _{ch}		150	°C
Storage Temperature	T _{stg}		-55 to +150	°C

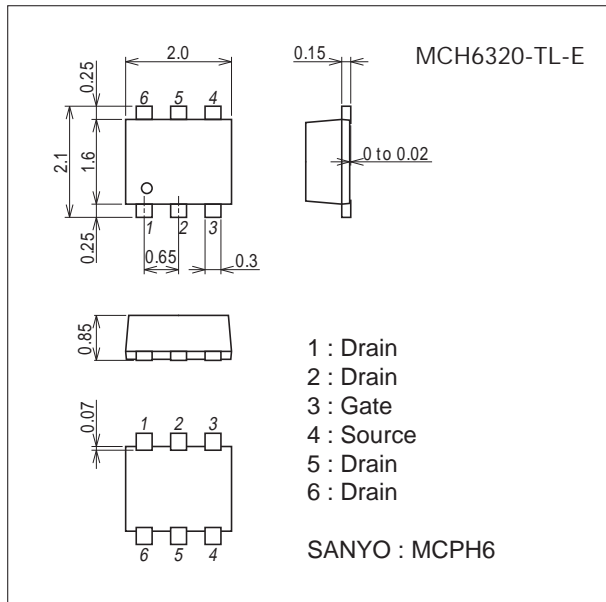
This product is designed to "ESD immunity < 200V**", so please take care when handling.

* Machine Model

Package Dimensions

unit : mm (typ)

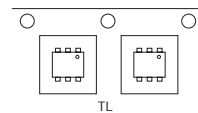
7022A-009



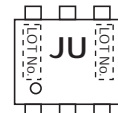
Product & Package Information

- Package : MCPH6
- JEITA, JEDEC : SC-88, SC-70-6, SOT-363
- Minimum Packing Quantity : 3,000 pcs./reel

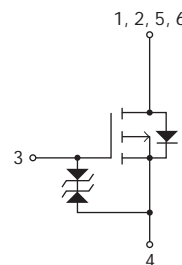
Packing Type : TL



Marking



Electrical Connection

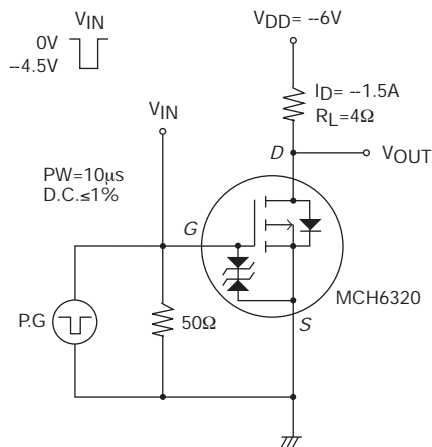


MCH6320

Electrical Characteristics at Ta=25°C

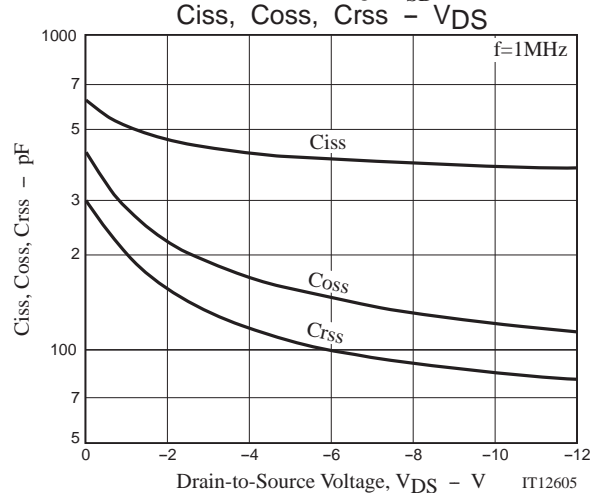
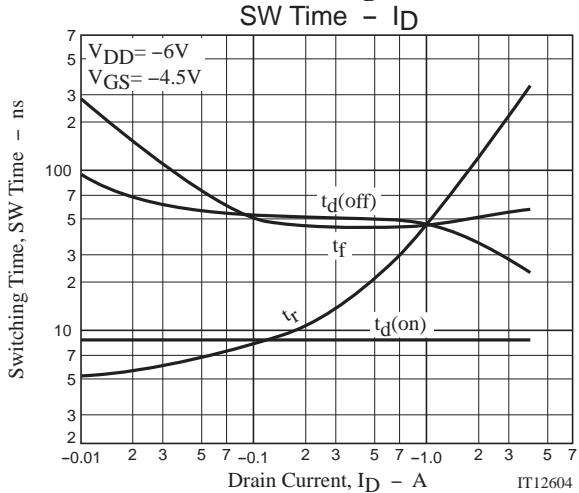
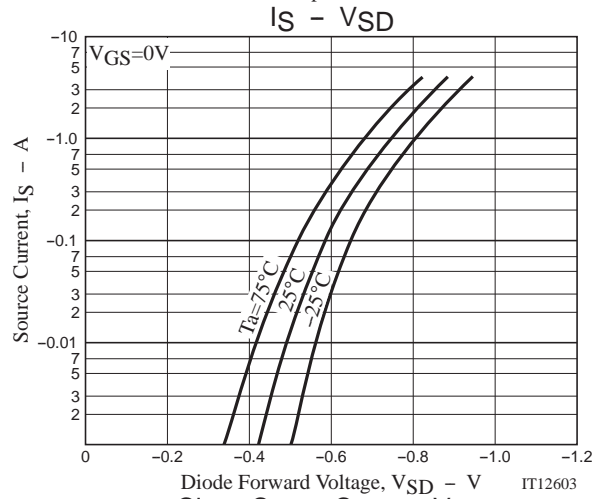
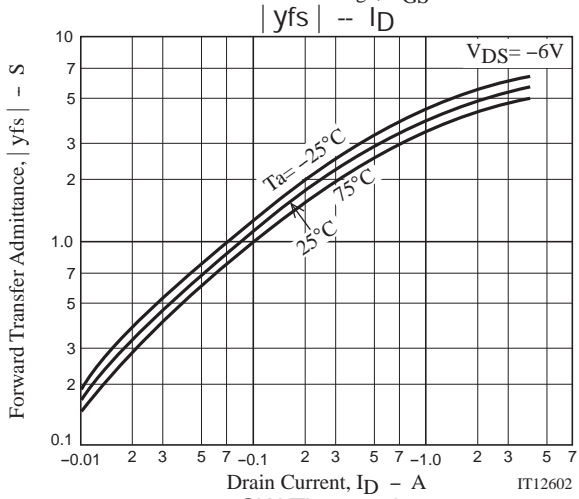
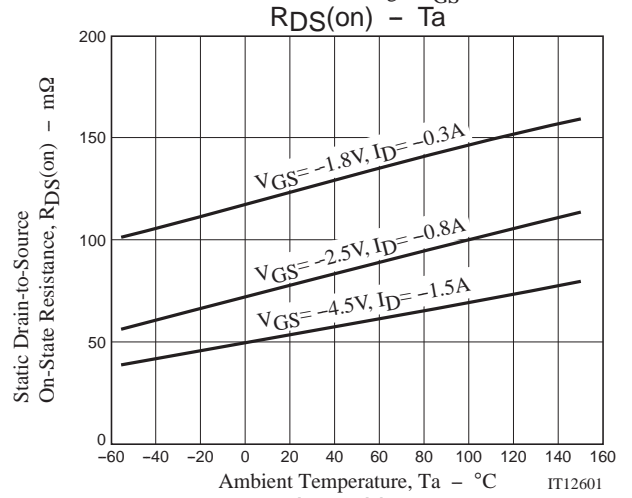
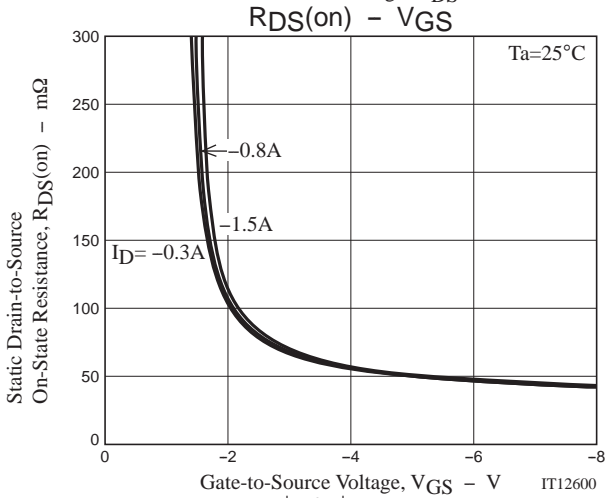
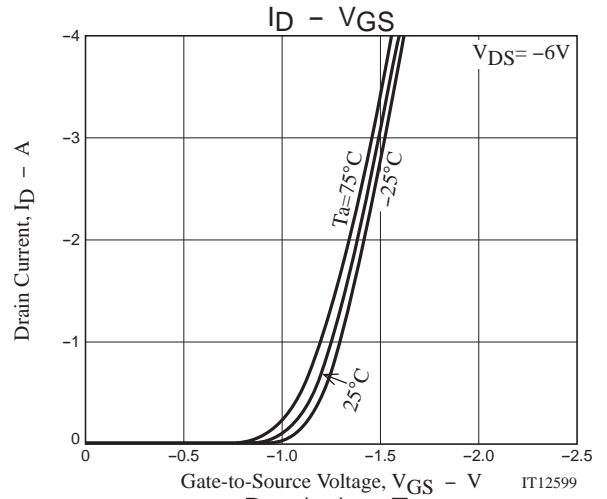
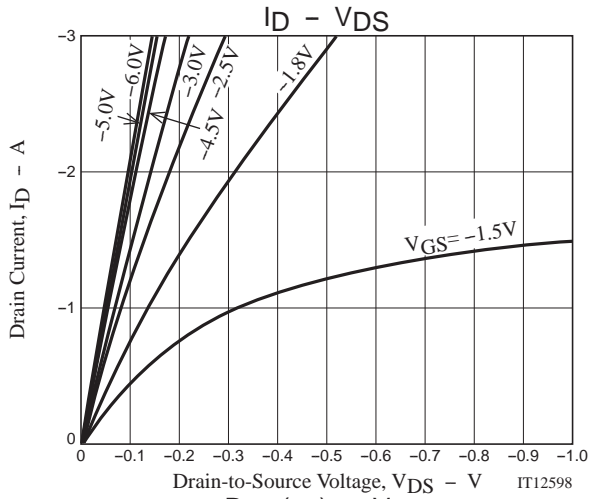
Parameter	Symbol	Conditions	Ratings			Unit
			min	typ	max	
Drain-to-Source Breakdown Voltage	V(BR)DSS	I _D =-1mA, V _{GS} =0V	-12			V
Zero-Gate Voltage Drain Current	I _{DSS}	V _{DS} =-12V, V _{GS} =0V			-10	μA
Gate-to-Source Leakage Current	I _{GSS}	V _{GS} =±8V, V _{DS} =0V			±10	μA
Cutoff Voltage	V _{GS(off)}	V _{DS} =-6V, I _D =-1mA	-0.4		-1.4	V
Forward Transfer Admittance	y _{fs}	V _{DS} =-6V, I _D =-1.5A	2.7	4.5		S
Static Drain-to-Source On-State Resistance	R _{DS(on)1}	I _D =-1.5A, V _{GS} =-4.5V		54	70	mΩ
	R _{DS(on)2}	I _D =-0.8A, V _{GS} =-2.5V		80	115	mΩ
	R _{DS(on)3}	I _D =-0.3A, V _{GS} =-1.8V		125	215	mΩ
Input Capacitance	C _{iss}	V _{DS} =-6V, f=1MHz		405		pF
Output Capacitance	C _{oss}			145		pF
Reverse Transfer Capacitance	C _{rss}			100		pF
Turn-ON Delay Time	t _{d(on)}		See specified Test Circuit.		8.8	
Rise Time	t _r			80		ns
Turn-OFF Delay Time	t _{d(off)}			41		ns
Fall Time	t _f			50		ns
Total Gate Charge	Q _g	V _{DS} =-6V, V _{GS} =-4.5V, I _D =-3.5A			5.6	
Gate-to-Source Charge	Q _{gs}			0.7		nC
Gate-to-Drain "Miller" Charge	Q _{gd}			1.6		nC
Diode Forward Voltage	V _{SD}	I _S =-3.5A, V _{GS} =0V		-0.86	-1.2	V

Switching Time Test Circuit

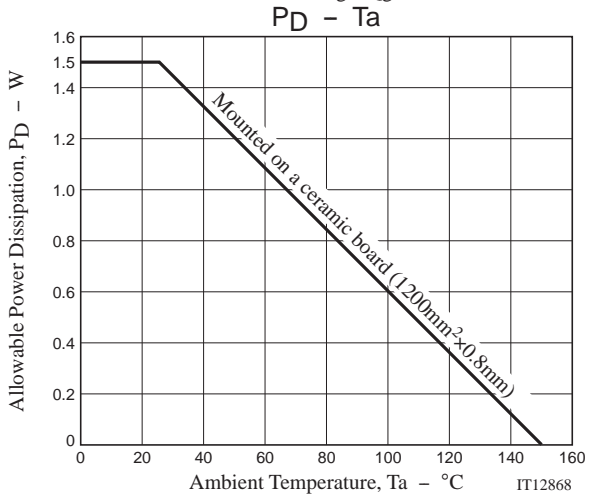
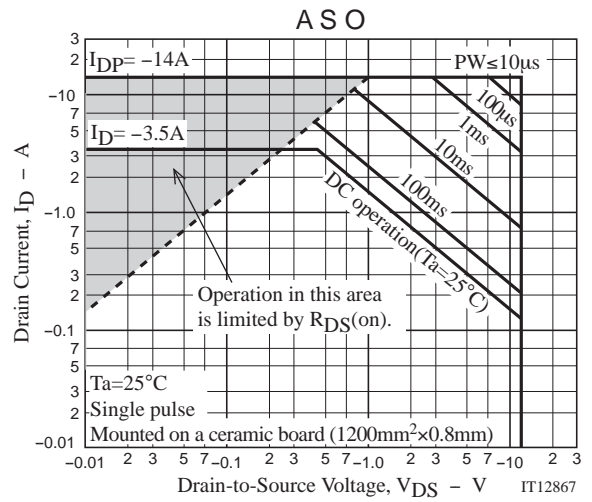
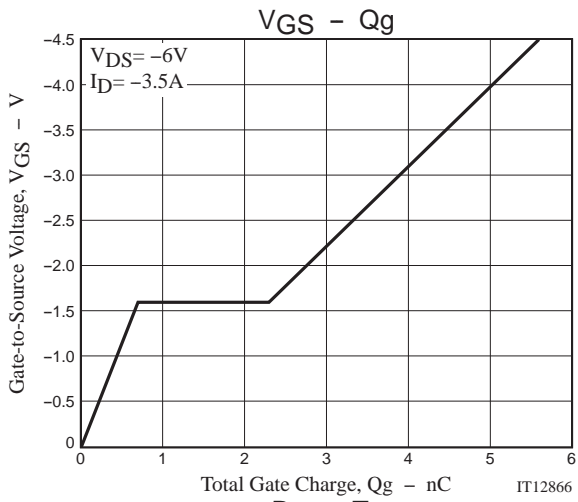


Ordering Information

Device	Package	Shipping	memo
MCH6320-TL-E	MCPH6	3,000pcs./reel	Pb Free



MCH6320



Taping Specification

MCH6320-TL-E

1. Packing Format

Package Name	Carrier Tape Type	Maximum Number of devices contained (pcs)			Packing format	
		Reel	Inner box	Outer box	Inner BOX (C-1)	Outer BOX (A-7)
MCPH6	MCP4	3,000	15,000	90,000	5 reels contained Dimensions:mm (external) 183×72×185	6 inner boxes contained Dimensions:mm (external) 440×195×210

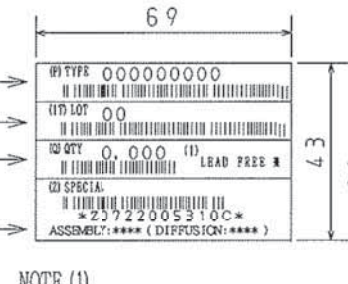
Packing method



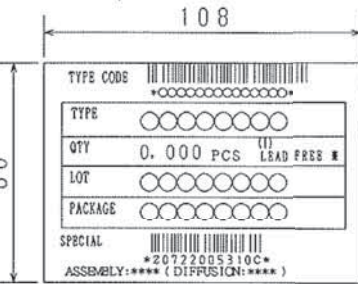
Type No.
LOT No.
Quantity
Origin

Reel label

Reel label, Inner box label
(unit:mm)



Outer box label
(It is a label at the time of factory shipments. The form of a label may change in physical distribution process.)



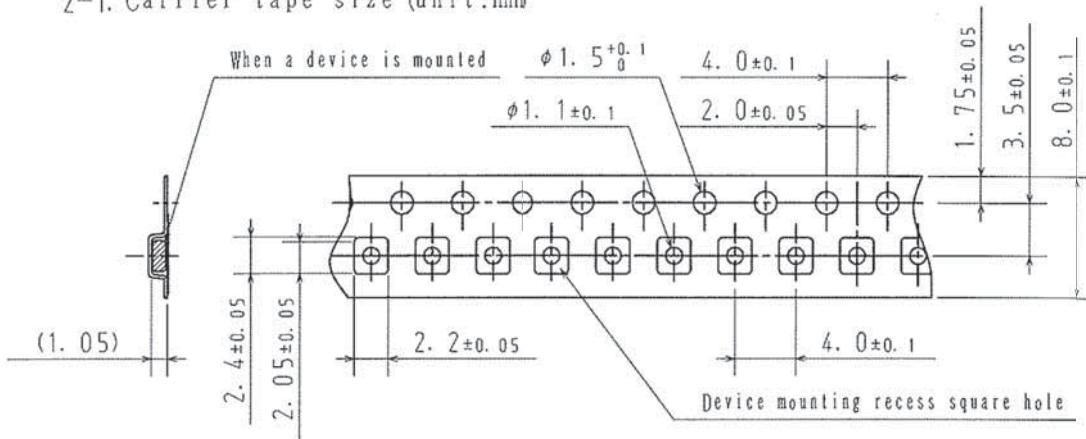
NOTE (1)

The LEAD FREE * description shows that the surface treatment of the terminal is lead free.

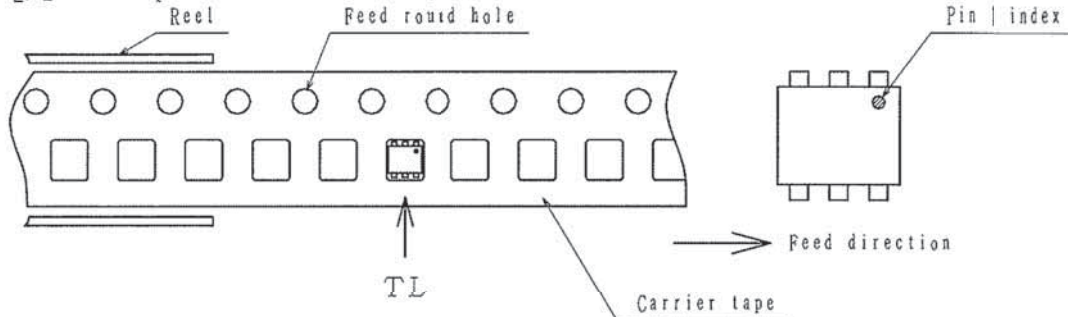
Label	JEITA Phase
LEAD FREE 3	JEITA Phase 3A
LEAD FREE 4	JEITA Phase 3

2. Taping configuration

2-1. Carrier tape size (unit:mm)



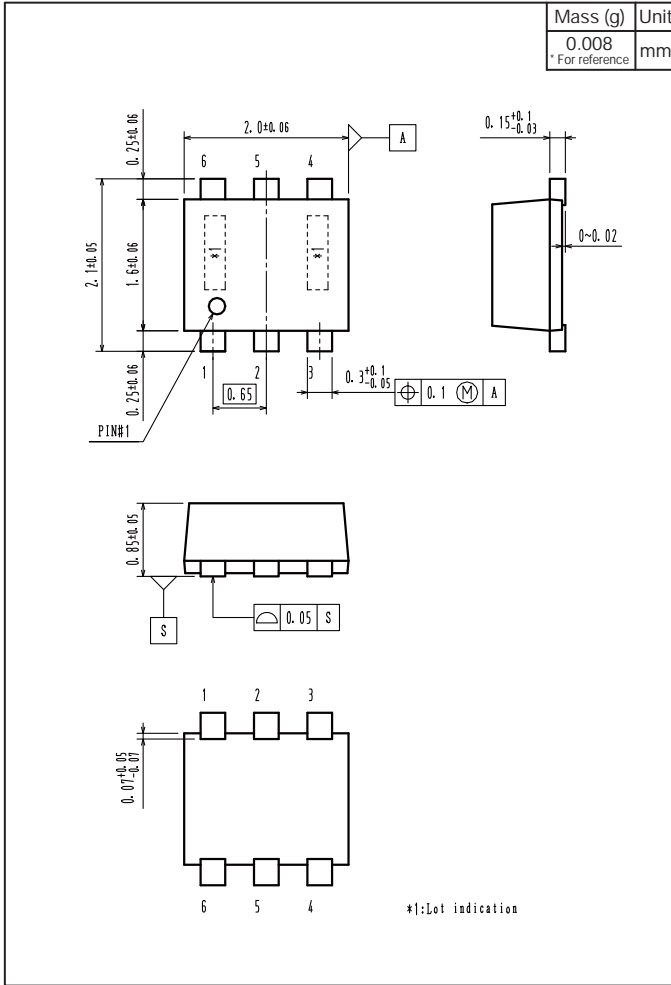
2-2. Device placement direction



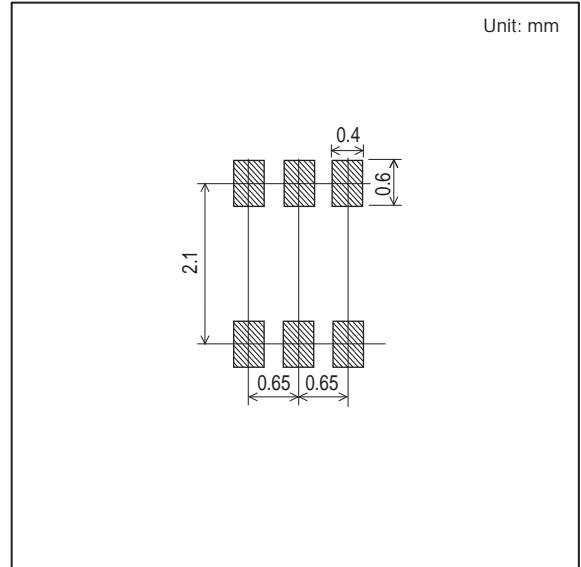
Those with pin | index on the feed hole side.....TL

MCH6320

Outline Drawing MCH6320-TL-E



Land Pattern Example



Note on usage : Since the MCH6320 is a MOSFET product, please avoid using this device in the vicinity of highly charged objects.

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